RoHS HAL

PB Green

Silicon Carbide Power MOSFET N-Channel Enhancement Mode

Features

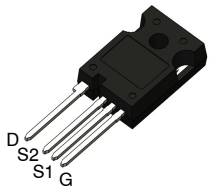
- 3rd Generation SiC MOSFET technology
- High blocking voltage with low on-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant

Typical Applications

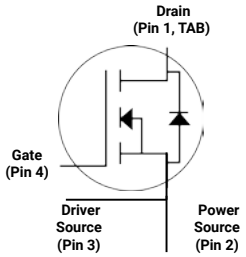
- EV charging
- Server power supplies
- Solar PV inverters
- UPS
- DC/DC converters

Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency
- Easy to parallel and simple to drive
- Enable new hard switching PFC topologies (Totem-Pole)



TO-247-4L



ORDERING INFORMATION

HT39N650AKZ

T_A = -40° to 175° C for all packages

Key Parameters

Parameter	Symbol	Min.	Typ.	Max	Unit	Conditions	Note
Drain - Source Voltage	V_{DS}			650	v	T_C = 25°C	
Maximum Gate - Source Voltage	$V_{GS(max)}$	-8		+19		Transient	
Operational Gate-Source Voltage	$V_{GS\,op}$		-4/15			Static	Note 1
DC Continuous Drain Current	I_D			39	A	V_{GS} = 15 V, T_C = 25 °C, T_J ≤175 °C	Fig. 19 Note 2
				27		V_{GS} = 15 V, T_C = 100 °C, T_J ≤175 °C	
Pulsed Drain Current	I_{DM}			99		t_{Pmax} limited by T_{jmax} V_{GS} = 15V, T_C = 25 °C	Fig. 22
Power Dissipation	P_D			150	W	T_C = 25 °C, T_J = 175 °C	Fig. 20
Operating Junction and Storage Temperature	T_J, T_{stg}			-40 to +175	°C		
Solder Temperature	T_L			260		According to JEDEC J-STD-020	
Mounting Torque	M_D			1 8.8	Nm lbf-in	M3 or 6-32 screw	

Note (1): Recommended turn-on gate voltage is 15V with ±5% regulation tolerance, see Application Note PRD-04814 for additional details
Note (2): Verified by design

Electrical Characteristics (T_C = 25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Note
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	650	—	—	V	V_{GS} = 0 V, I_D = 100 μA	
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.3	3.6	V	V_{DS} = V_{GS}, I_D = 5 mA	Fig. 11
		—	1.9	—		V_{DS} = V_{GS}, I_D = 5 mA, T_J = 175℃	
Zero Gate Voltage Drain Current	I_{DSS}	—	1	50	μA	V_{DS} = 650 V, V_{GS} = 0 V	
Gate-Source Leakage Current	I_{GSS}	—	10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
Drain-Source On-State Resistance	$R_{DS(on)}$	42	60	79	mΩ	V_{GS} = 15 V, I_D = 13.2 A	Fig. 4, 5, 6
		—	80	—		V_{GS} = 15 V, I_D = 13.2 A, T_J = 175°C	
Transconductance	g_{fs}	—	10	—	S	V_{DS} = 20 V, I_{DS} = 13.2 A	Fig. 7
			9			V_{DS} = 20 V, I_{DS} = 13.2 A, T_J = 175°C	
Input Capacitance	C_{iss}	—	1020	—	pF	V_{GS} = 0 V, V_{DS} = 600 V f = 1 Mhz V_{AC} = 25 mV	Fig. 17, 18
Output Capacitance	C_{oss}	—	80	—			
Reverse Transfer Capacitance	C_{rss}	—	9	—			
Effective Output Capacitance (Energy Related)	$C_{o(er)}$	—	95	—		V_{GS} = 0 V, V_{DS} = 0 V to 400 V	Note 3
Effective Output Capacitance (Time Related)	$C_{o(tr)}$	—	132	—			
C_{oss} Stored Energy	E_{oss}	—	15	—	μJ	V_{DS} = 600 V, f = 1 Mhz	Fig. 16
Turn-On Switching Energy (Body Diode)	E_{on}	—	70	—		V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 13.2 A, $R_{G(ext)}$ = 2.5 Ω, L= 135 μH, T_J = 175°C FWD = Internal Body Diode of MOSFET	Fig. 25
Turn Off Switching Energy (Body Diode)	E_{off}	—	5	—			
Turn-On Switching Energy (External Sic Diode)	E_{on}	—	67	—		V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 13.2 A, $R_{G(ext)}$ = 2.5 Ω, L= 135 μH, T_J = 175°C FWD = External SiC DIODE	
Turn Off Switching Energy (External Sic Diode)	E_{off}	—	6	—			
Turn-On Delay Time	$t_{d(on)}$	—	8	—	ns	V_{DD} = 400 V, V_{GS} = -4 V/15 V I_D = 13.2 A, $R_{G(ext)}$ = 2.5 Ω, L= 135 μH Timing relative to V_{DS} Inductive load	Fig. 26
Rise Time	t_r	—	11	—			
Turn-Off Delay Time	$t_{d(off)}$	—	17	—			
Fall Time	t_f	—	5	—			
Internal Gate Resistance	$R_{G(int)}$	—	3	—	Ω	f = 1 MHz, V_{AC} = 25 mV	
Gate to Source Charge	Q_{gs}	—	13	—	nC	V_{DS} = 400 V, V_{GS} = -4 V/15 V I_D = 13.2 A Per IEC60747-8-4 pg 21	Fig. 12
Gate to Drain Charge	Q_{gd}	—	17	—			
Total Gate Charge	Q_g	—	46	—			

Note:

[3] $C_{o(er)}$, a lumped capacitance that gives same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V
$C_{o(tr)}$, a lumped capacitance that gives same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Reverse Diode Characteristics (T_C = 25°C unless otherwise specified)

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Notes
Diode Forward Voltage, T_J = 25°C	V_{SD}	5.1	—	V	V_{GS} = -4 V, I_{SD} = 6.6 A, T_J=25C	Fig. 8, 9, 10
Diode Forward Voltage, T_J = 175°C		4.8	—		V_{GS} = -4 V, I_{SD} = 6.6 A, T_J=175C	
Continuous Diode Forward Current	I_S	—	23	A	V_{GS} = -4 V, T_J = 25°C	
Diode pulse Current	I_{SM}	—	99		V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	
Reverse Recovery Time	t_{rr}	11	—	ns	V_{GS} = -4 V, I_{SD} = 13.2 A, V_R = 400 V di_F/dt = 4500 A/µs, T_J = 175°C	
Reverse Recovery Charge	Q_{rr}	151	—	nC		
Peak Reverse Recovery Current	I_{RRM}	27	—	A		
Reverse Recovery Time	t_{rr}	16	—	ns	V_{GS} = -4 V, I_{SD} = 13.2 A, V_R = 400 V di_F/dt = 2400 A/µs, T_J = 175°C	
Reverse Recovery Charge	Q_{rr}	110	—	nC		
Peak Reverse Recovery Current	I_{RRM}	12	—	A		

Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.99	°C/W	Fig. 21
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	40		

Typical Performance

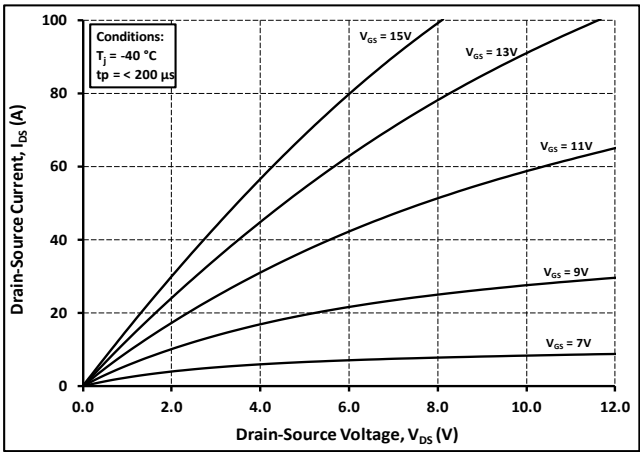


Figure 1. Output Characteristics T_J = -40°C

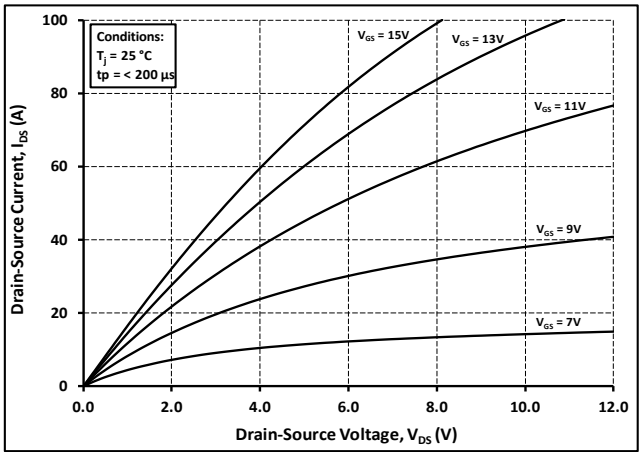


Figure 2. Output Characteristics T_J = 25°C

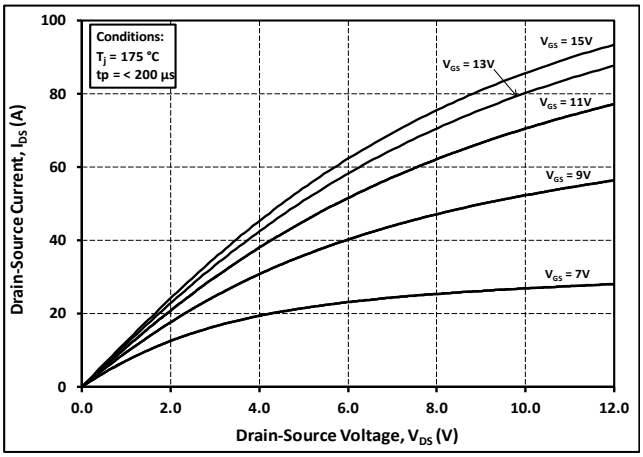


Figure 3. Output Characteristics T_J = 175°C

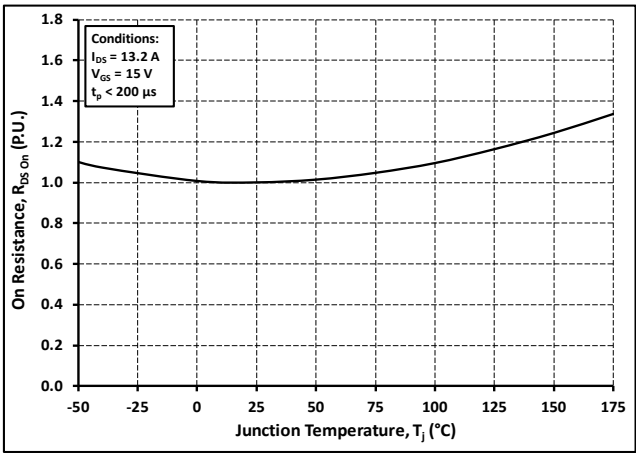


Figure 4. Normalized On-Resistance vs. Temperature

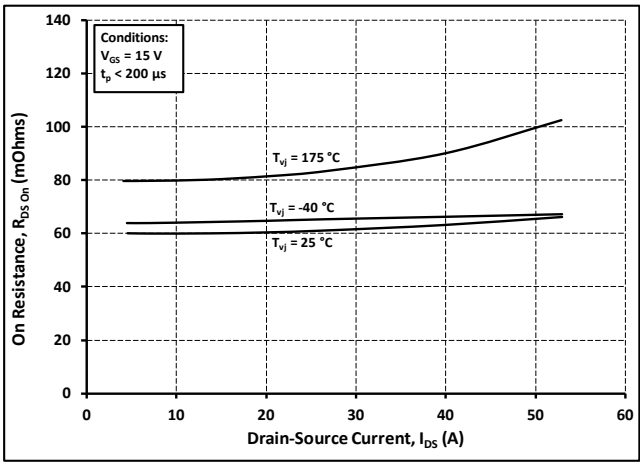


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

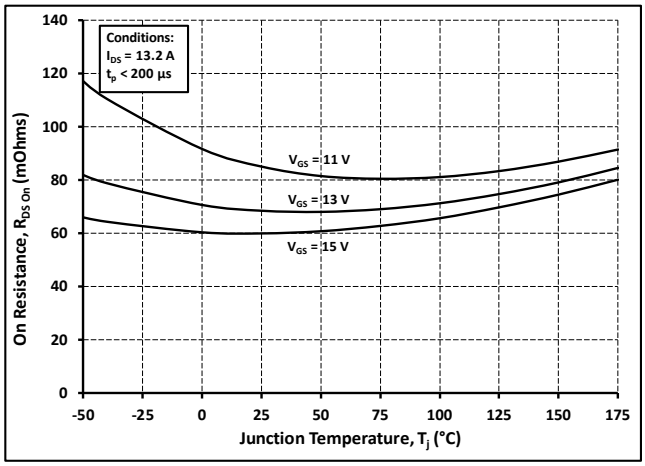


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

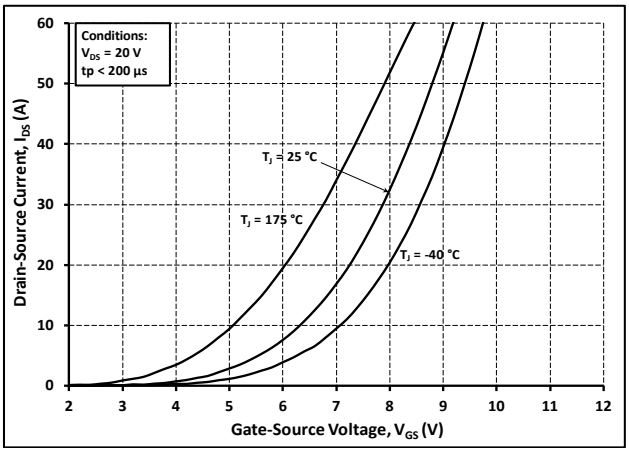


Figure 7. Transfer Characteristic for Various Junction Temperatures

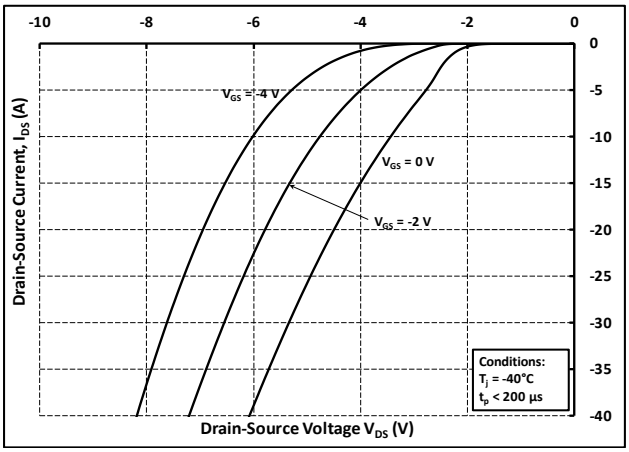


Figure 8. Body Diode Characteristic at -40°C

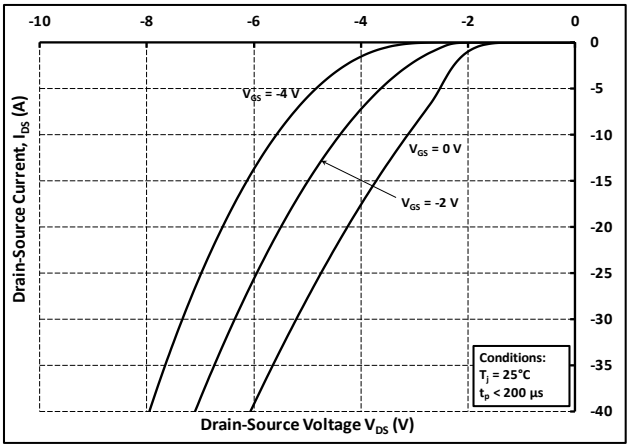


Figure 9. Body Diode Characteristic at 25°C

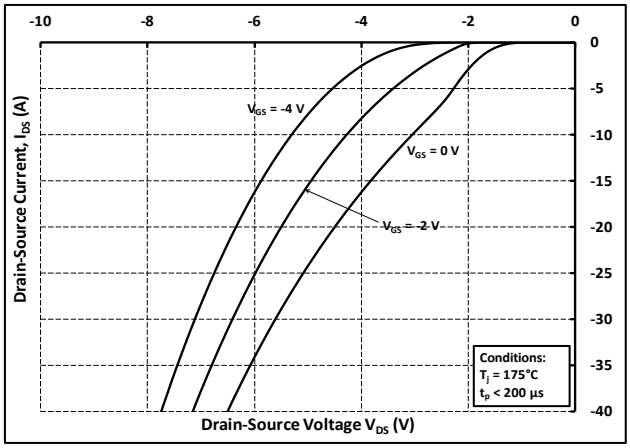


Figure 10. Body Diode Characteristic at 175°C

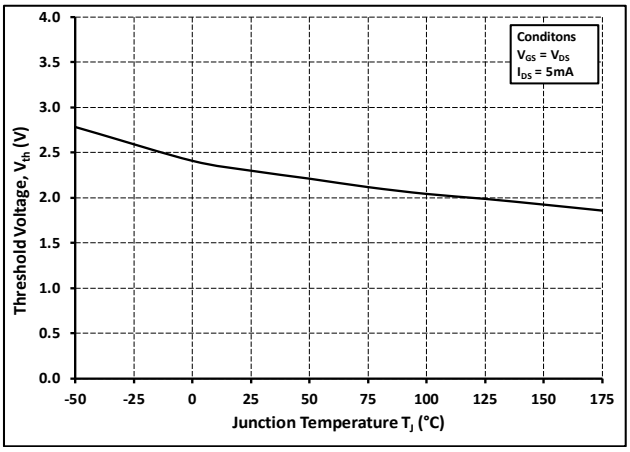


Figure 11. Threshold Voltage vs. Temperature

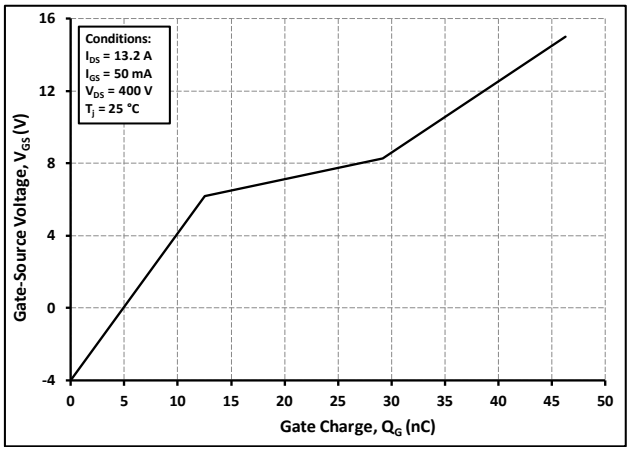


Figure 12. Gate Charge Characteristics

Typical Performance

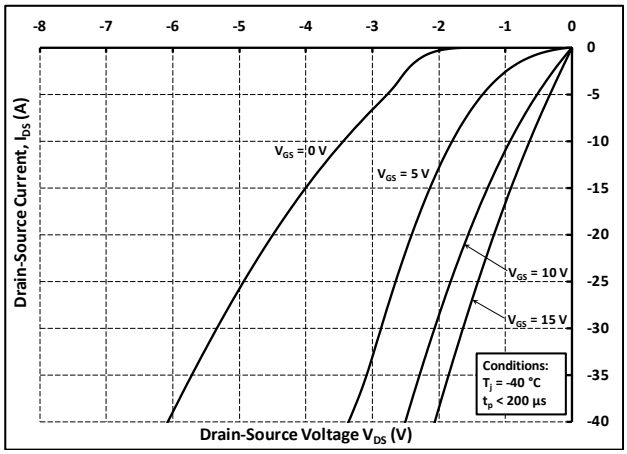


Figure 13. 3rd Quadrant Characteristic at -40°C

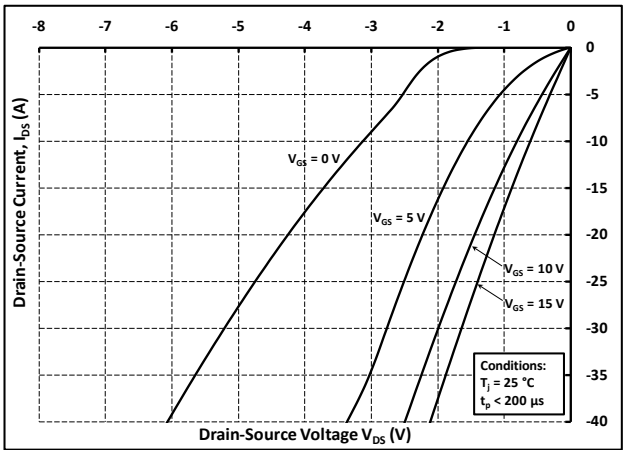


Figure 14. 3rd Quadrant Characteristic at 25°C

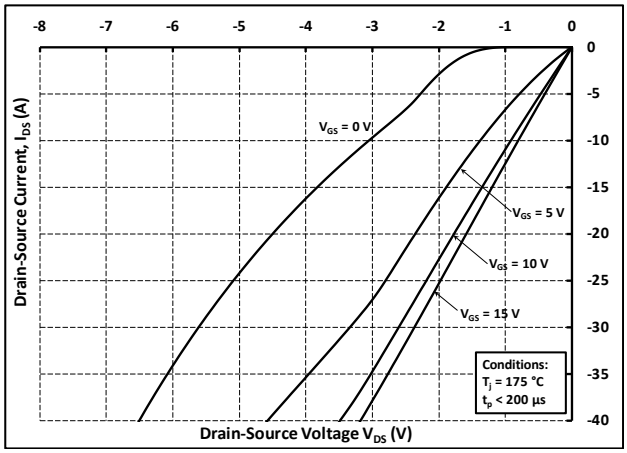


Figure 15. 3rd Quadrant Characteristic at 175°C

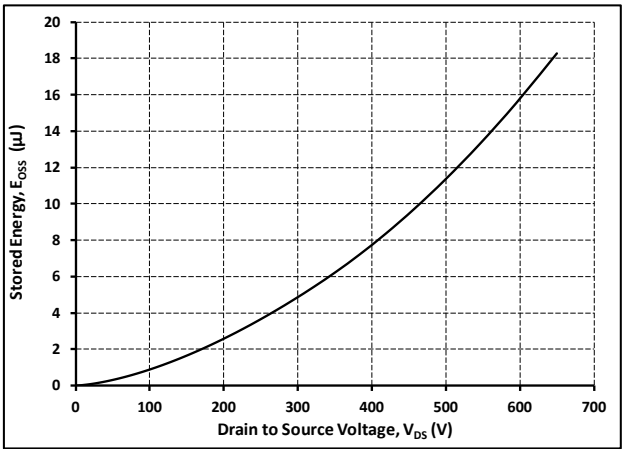


Figure 16. Output Capacitor Stored Energy

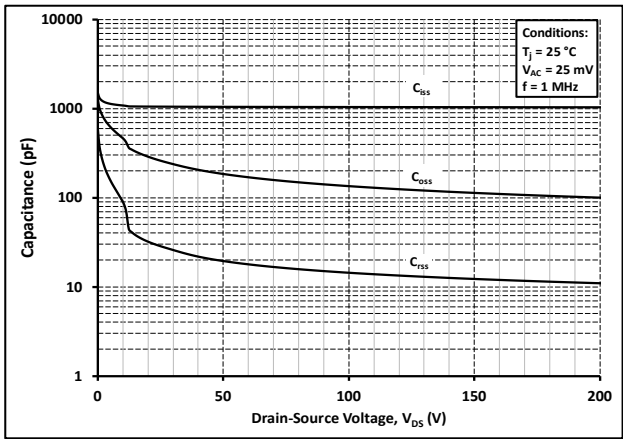


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200 V)

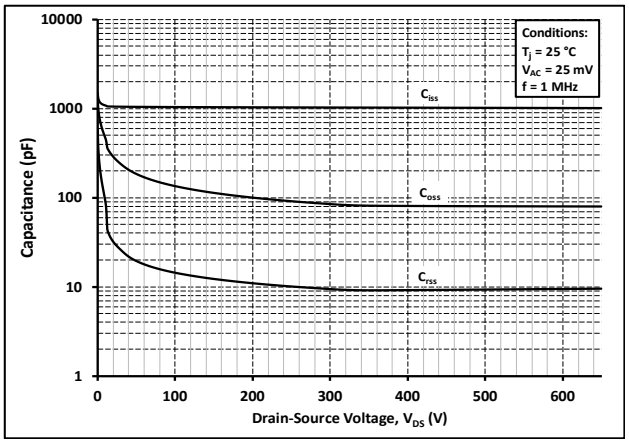


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 650 V)

Typical Performance

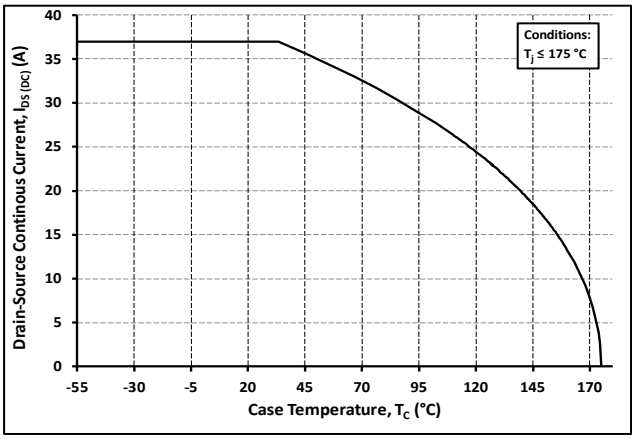


Figure 19. Continuous Drain Current Derating vs. Case Temperature

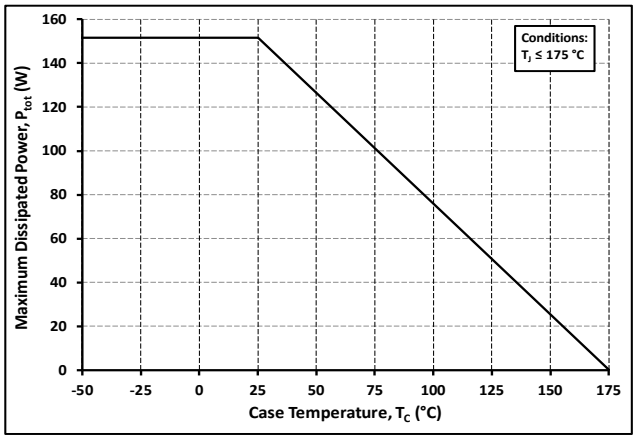


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

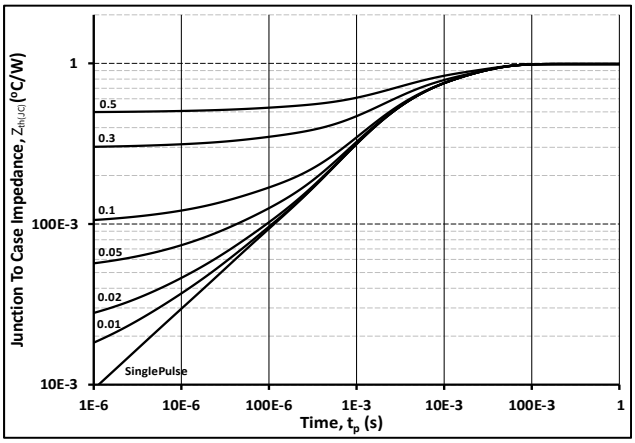


Figure 21. Transient Thermal Impedance (Junction - Case)

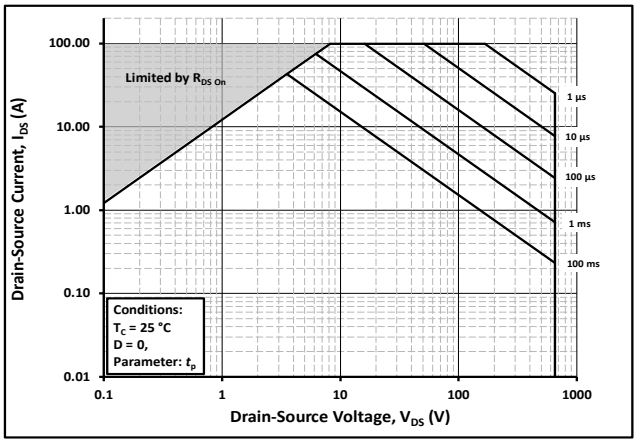


Figure 22. Safe Operating Area

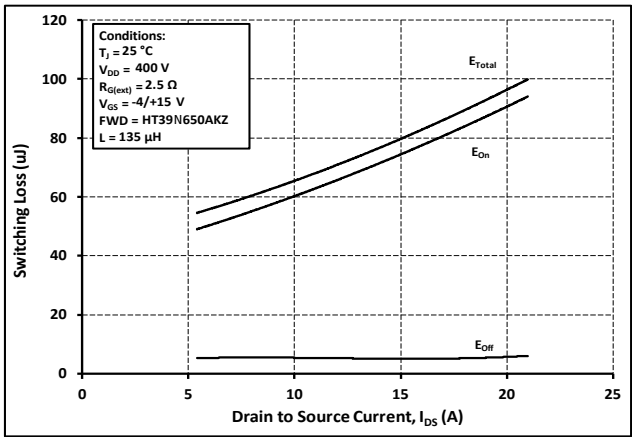


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 400 V)

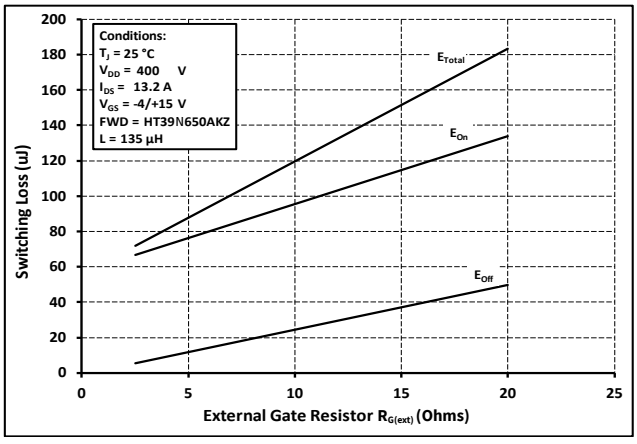


Figure 24. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

Typical Performance

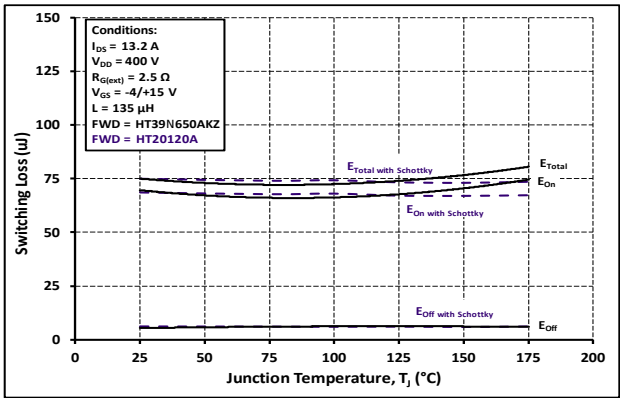


Figure 25. Clamped Inductive Switching Energy vs. Temperature

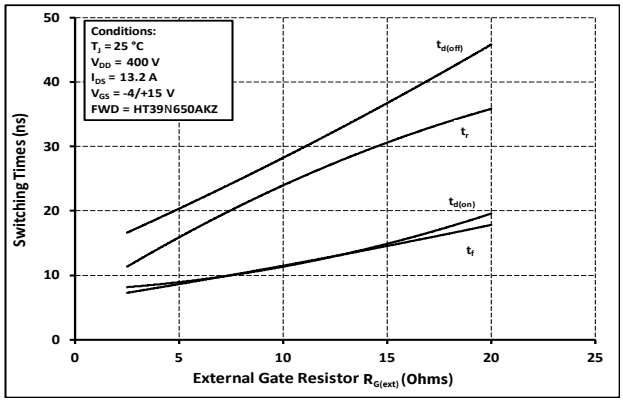


Figure 26. Switching Times vs. $R_{G(ext)}$

Test Circuit Schematic

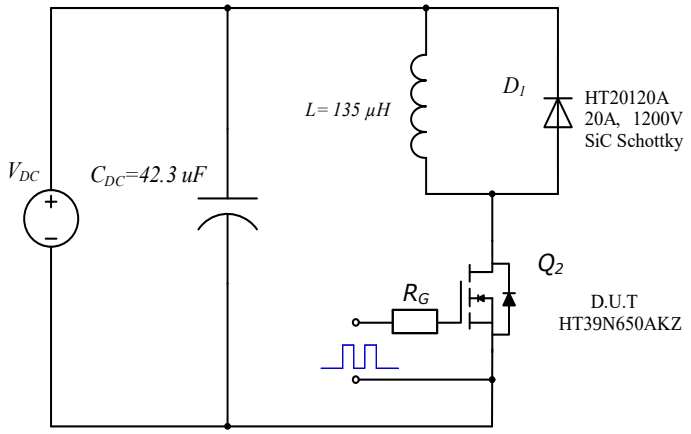


Figure 27. Clamped Inductive Switching Waveform Test Circuit

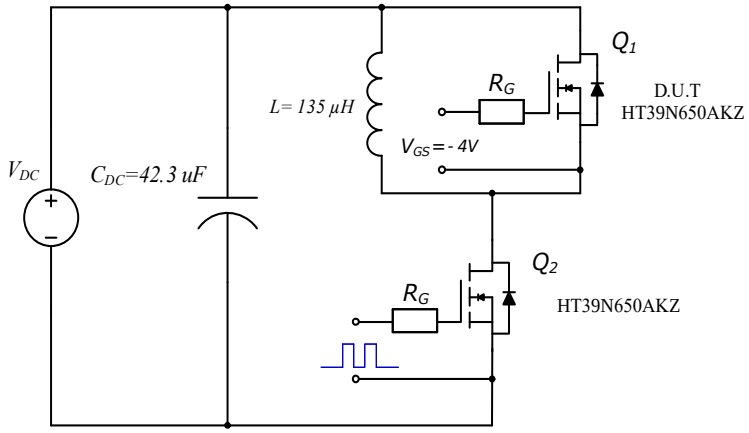
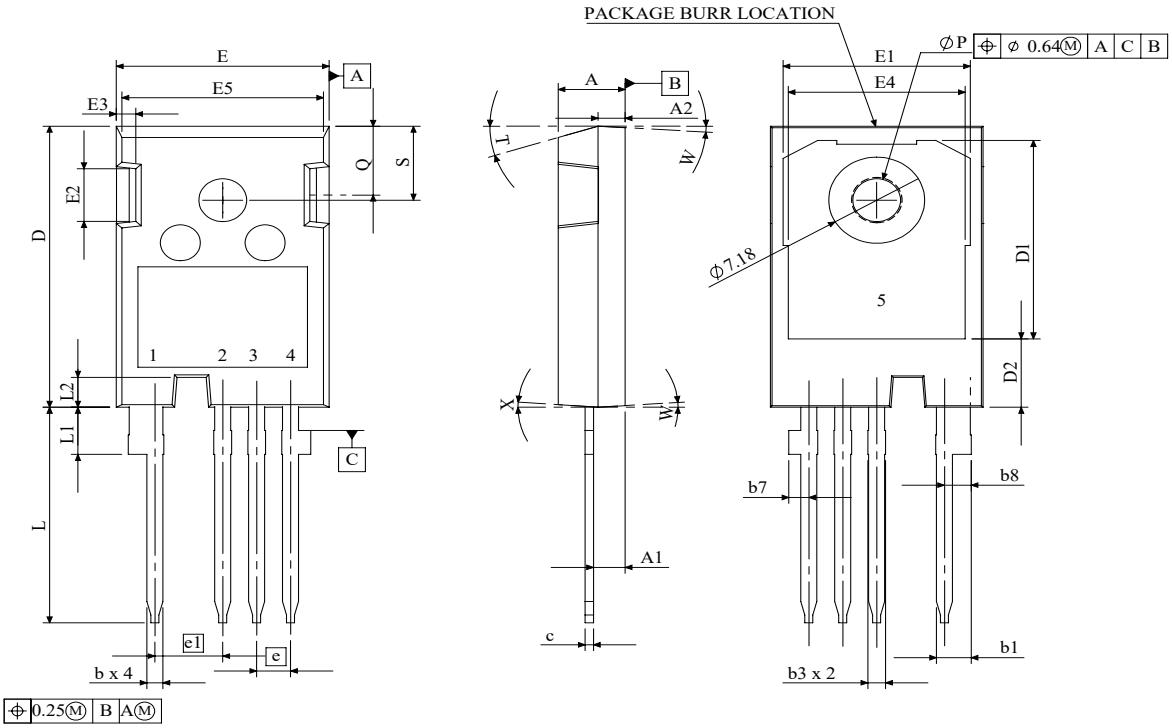


Figure 28. Body Diode Recovery Test Circuit

Package Dimensions

Package TO-247-4L



SYMBOL	MIN (mm)	MAX (mm)
A	4.83	5.21
A1	2.23	2.54
A2	1.91	2.16
b	1.07	1.33
b1	2.39	2.94
b3	1.07	1.60
b7	1.30	1.70
b8	1.80	2.20
c	0.55	0.68
D	23.30	23.63
D1	16.25	17.65
D2	5.55	5.95
E	15.75	16.13
E1	13.1	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
E5	14.65	15.05
e1	5.08 BSC	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF.	
W	3.5° REF.	
X	4° REF.	

1	DRAIN
2	SOURCE
3	DRIVER SOURCE
4	GATE
5	DRAIN

NOTE:

1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. BURR OR MOLD FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

Recommended Solder Pad Layout